

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC2236

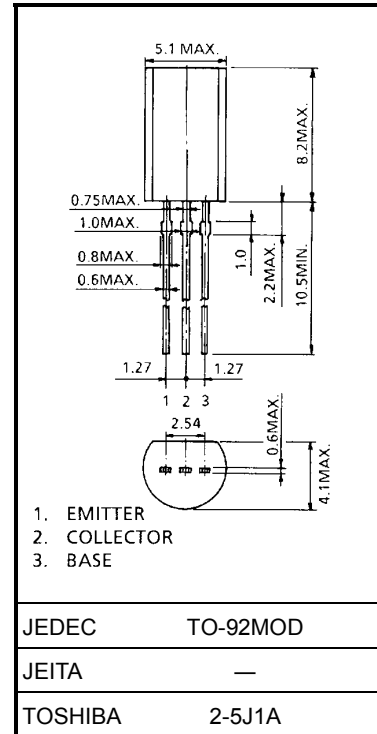
## Audio Power Amplifier Applications

Unit: mm

- Complementary to 2SA966 and 3-watt output applications.

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	30	V
Collector-emitter voltage	$V_{CEO}$	30	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	1.5	A
Base current	$I_B$	0.15	A
Collector power dissipation	$P_C$	900	mW
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55 to 150	°C



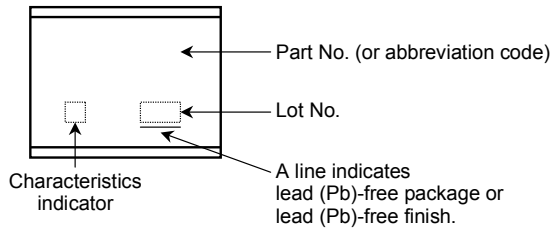
Weight: 0.36 g (typ.)

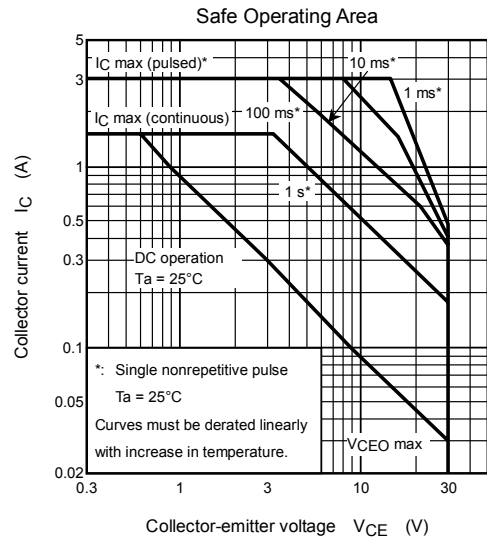
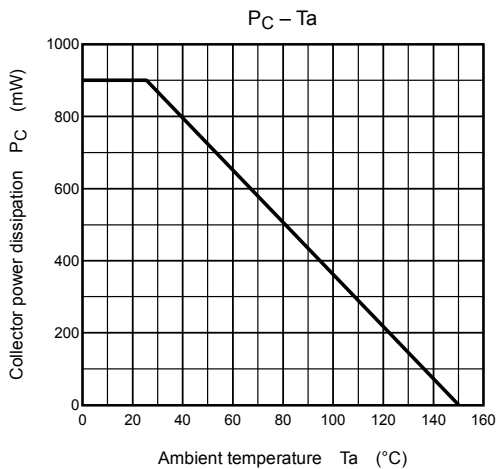
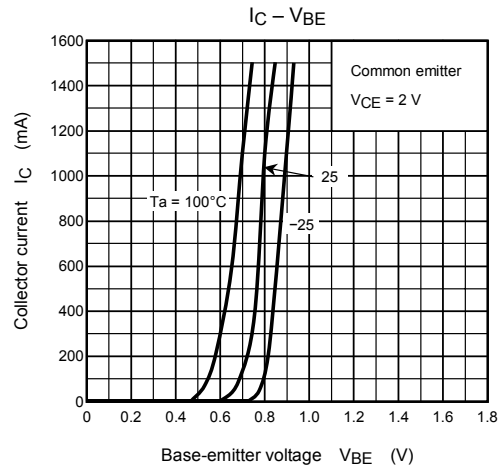
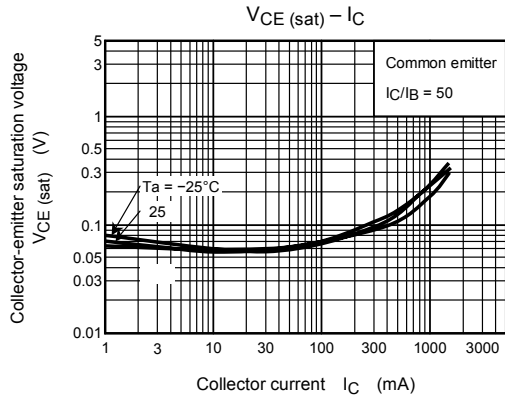
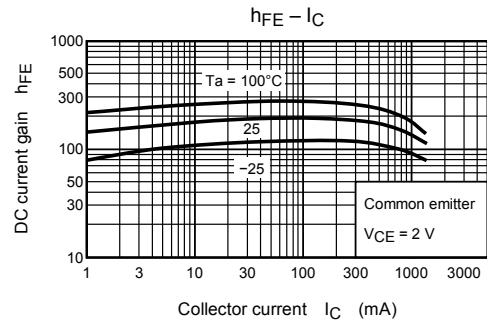
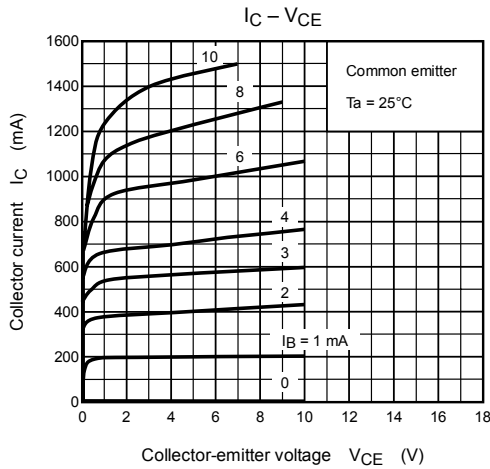
### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 30\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	30	—	—	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1\text{ mA}, I_C = 0$	5	—	—	V
DC current gain	$h_{FE}$ (Note)	$V_{CE} = 2\text{ V}, I_C = 500\text{ mA}$	100	—	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1.5\text{ A}, I_B = 0.03\text{ A}$	—	—	2.0	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = 2\text{ V}, I_C = 500\text{ mA}$	—	—	1.0	V
Transition frequency	$f_T$	$V_{CE} = 2\text{ V}, I_C = 500\text{ mA}$	—	120	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	—	30	pF

Note:  $h_{FE}$  classification O: 100 to 200, Y: 160 to 320

## Marking





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